



THE DATASHEET OF BUK221-50DY

BUK221-50DY

Dual channel high-side TOPFET™

Rev. 01 — 16 April 2003

Product data

1. Product profile

1.1 Description

Monolithic temperature and overload protected dual high-side power switch based on TOPFET™ Trench technology in a 7-pin surface mount plastic package.

Product availability:

BUK221-50DY in SOT427 (D²-PAK).

1.2 Features

- Very low quiescent current
- Power TrenchMOS™
- Overtemperature protection
- Over and undervoltage protection
- Reverse battery protection
- Low charge pump noise
- Loss of ground protection
- Negative load clamping
- CMOS logic compatibility
- Current limitation
- Latched overload protection
- ESD protection for all pins
- Diagnostic status indication
- Off-state open load detection
- Load dump protection
- Internal ground resistor.

1.3 Applications

- 12 and 24 V grounded loads
- Inductive loads
- High inrush current loads
- Replacement for relays and fuses.

1.4 Quick reference data

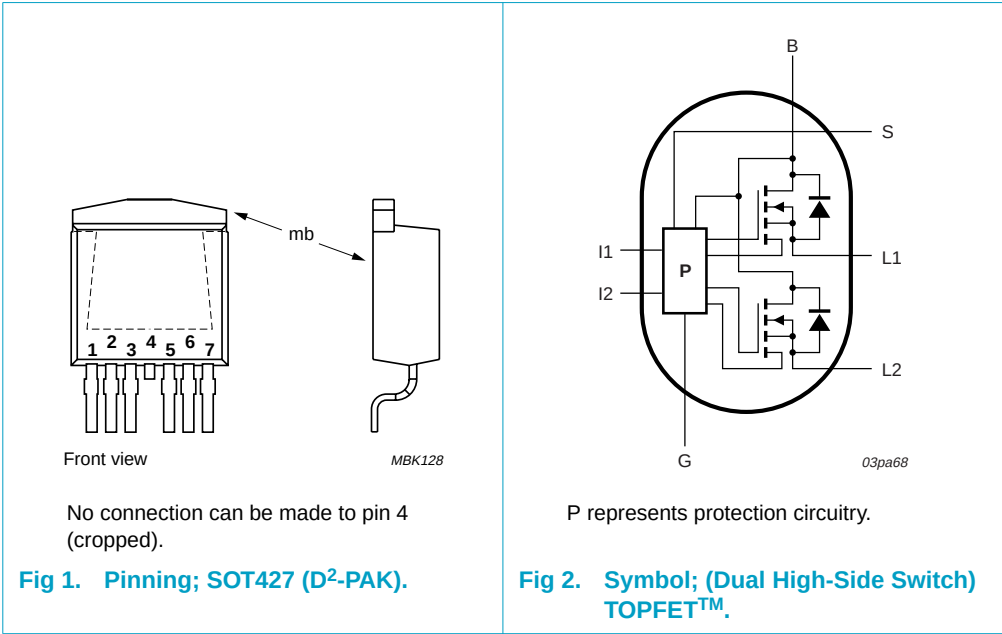
Table 1: Quick reference data

Symbol	Parameter	Min	Max	Units
R _{BLon}	battery-load on-state resistance	-	90	mΩ
I _L	load current	-	4	A
I _{L(nom)}	nominal load current (ISO)	3.6	-	A
I _{L(lim)}	self-limiting load current	8	16	A
V _{BG(oper)}	battery-ground operating voltage	5.5	35	V



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2. Pinning information



2.1 Pin description

Table 2: Pin description

Symbol	Pin	I/O	Description
L1	1	O	load 1
G	2	-	circuit common ground
I1	3	I	input 1
B	4	-	[1] [2] battery
S	5	O	status
I2	6	I	input 2
L2	7	O	load 2
-	mb	-	[2] mounting base

[1] Pin 4 is cropped and cannot be connected to the PCB by surface mounting.
[2] The battery is connected to the mounting base.

3. Block diagram

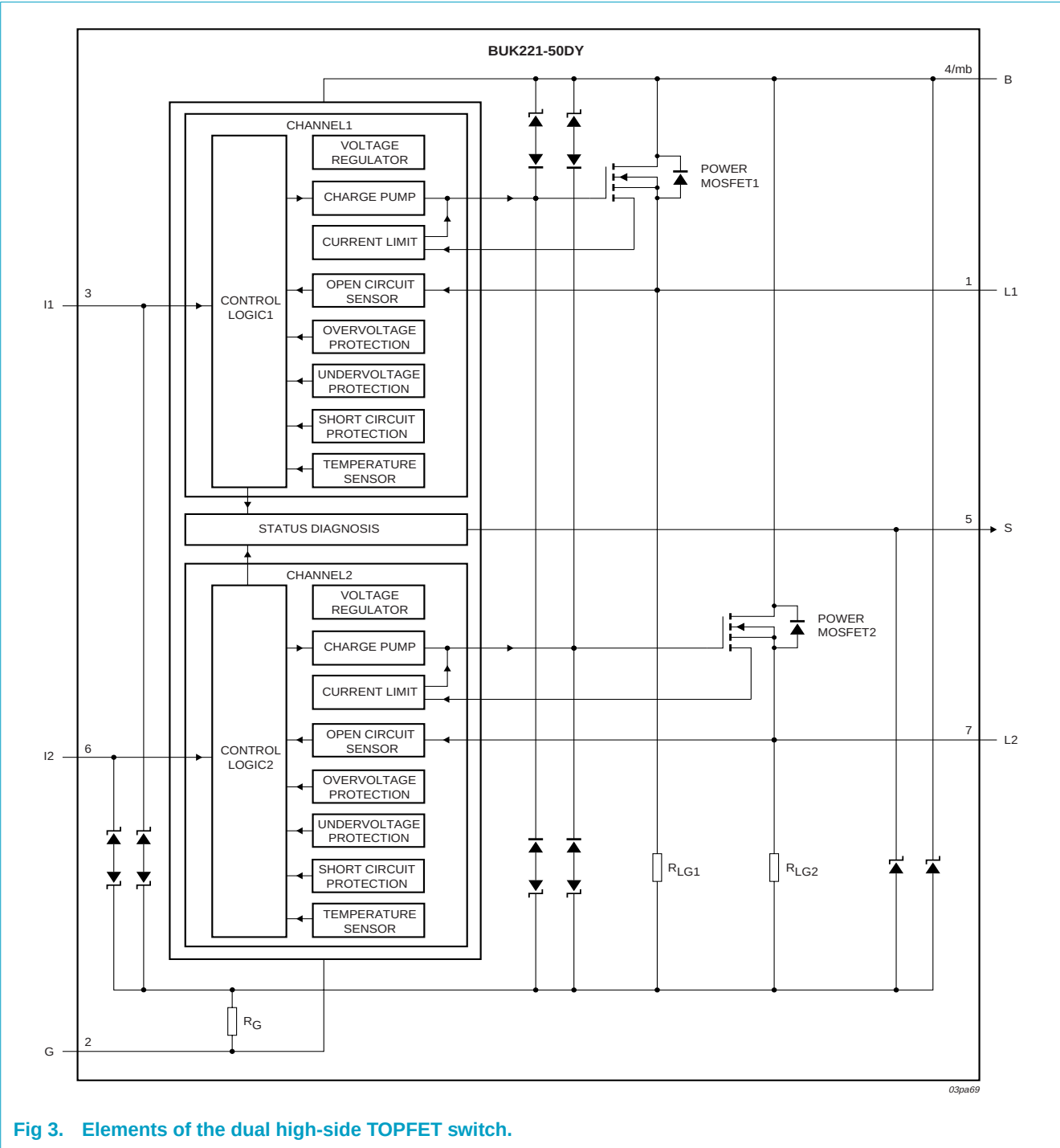


Fig 3. Elements of the dual high-side TOPFET switch.

4. Functional description

A diagnostic status ensures faster fault detection.

Active current limit is combined with latched short circuit protection in order to protect the device in the event of a short circuit.

Thermal shutdown for high temperature conditions has an automatic restart at a lower temperature so providing protection against excessive power dissipation.

Active clamping protects the device against low energy spikes.

Undervoltage lockout means the device shuts down for low battery voltages, thus avoiding faulty operation.

Overvoltage shutdown in the on-state protects a load such as a lamp filament from potentially destructive voltage spikes.

Table 3: Truth table

Abbreviations: L = logic LOW; H = logic HIGH; X = don't care; 0 = condition not present; 1 = condition present; UV = undervoltage; OV = overvoltage; OC = open circuit load; SC = short circuit; OT = overtemperature [1].

Input		Supply		Load 1			Load 2			Load output		Status	Operating mode
1	2	UV	OV	OC	SC	OT	OC	SC	OT	1	2		
L	L	0	X	0	X	X	0	X	X	OFF	OFF	H	both off & normal
L	L	0	X	1	X	X	X	X	X	OFF	OFF	L	both off, one/both OC or shorted to V_S or battery; Figure 10
L	H	0	X	1	X	X	0	0	0	OFF	ON	L	one off & OC, with other on & normal
H	L	0	0	0	0	0	0	0	0	ON	OFF	H	one on & normal, with other off & normal
H	H	0	0	0	0	0	0	0	0	ON	ON	H	both on & normal
H	X	1	0	X	X	X	0	X	X	OFF	OFF	H	supply undervoltage lockout
H	X	0	1	X	0	0	X	0	0	OFF	OFF	H	supply overvoltage shutdown
H	X	0	0	0	1	X	X	X	X	OFF	X	L	one SC tripped
H	L	0	0	0	1	X	0	0	X	OFF	OFF	L	one SC tripped, with other off & normal
H	H	0	0	0	1	X	0	0	0	OFF	ON	L	one SC tripped, with other on & normal
H	X	0	0	0	0	1	X	X	X	OFF	X	L	one OT shutdown
H	L	0	0	0	0	1	0	0	X	OFF	OFF	L	one OT shutdown, with other off & normal
H	H	0	0	0	0	1	0	0	0	OFF	ON	L	one OT shutdown, with other on & normal

[1] The status will continue to indicate OT (even if the input goes LOW) until the device cools below the reset threshold temperature. See "Overtemperature protection" characteristics in [Table 6 "Static characteristics"](#).

5. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{BG}	battery-ground supply voltage	T _{mb} ≤ 130 °C T _{mb} ≤ 25 °C during soldering (≤ 10 s)	[1] -	45	V
I _L	load current		-	4	A
P _{tot}	total power dissipation		-	44.6	W
T _{stg}	storage temperature		−55	+175	°C
T _j	junction temperature		−40	+150	°C
T _{mb}	mounting base temperature		-	260	°C
Reverse battery voltage					
V _{BGR}	reverse battery-ground supply voltage	R _I ≥ 3.3 kΩ; R _{SS} ≥ 3.3 kΩ; Figure 10	[2] -	16	V
V _{BGRR}	repetitive reverse battery-ground supply voltage		-	32	V
Input current					
I _I	input current		−5	+5	mA
I _{IRM}	repetitive peak input current	δ ≤ 0.1; t _p = 300 μs	−50	+50	mA
Status current					
I _S	status current		−5	+5	mA
I _{SRM}	repetitive peak status current	δ ≤ 0.1; t _p = 300 μs	−50	+50	mA
Inductive load clamping					
E _{BL(CL)S}	non-repetitive battery-load clamping energy	T _j = 150 °C prior to turn-off; V _{BG} = 13 V; I _L = 5 A; (one channel) Figure 13	-	60	mJ
Electrostatic discharge voltage					
V _{esd}	electrostatic discharge voltage	Human Body Model 1; C = 100 pF; R = 1.5 kΩ	-	2	kV

- [1] The device will not be harmed by exposure to the maximum supply voltage, but normal operation is not possible because of overvoltage shutdown - see **Table 6 “Static characteristics”** for the operating range.
- [2] Reverse battery voltage is only allowed with external resistors to limit the input and status currents to a safe value. The connected load must limit the reverse load current. The internal ground resistor limits the reverse battery ground current. See **Figure 10 “Typical dynamic response circuit diagram including reverse supply protection and open load detection.”**

6. Thermal characteristics

Table 5: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	per channel	-	4	5.6	K/W
		both channels	-	2	2.8	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on printed circuit board; minimum footprint	-	50	-	K/W

7. Static characteristics

Table 6: Static characteristics

Limits are valid for $-40\text{ °C} \leq T_{mb} \leq +150\text{ °C}$ and typical values for $T_{mb} = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Clamping voltage						
V _{BG(CL)}	battery-ground clamping voltage	I _G = 1 mA	45	55	65	V
V _{BL(CL)}	battery-load clamping voltage	I _L = I _G = 1 mA	50	55	65	V
V _{LG(CL)}	load-ground clamping voltage	I _L = 10 mA; Figure 13	[1] −18	−23	−28	V
		I _L = 4 A; t _p = 300 μs	−20	−25	−30	V
Supply voltage						
V _{BG(oper)}	battery-ground operating voltage		5.5	-	35	V
Current [2]						
I _B	battery quiescent current	V _{LG} = V _{IG} = 0 V; Figure 9	[3]			
		T _{mb} = 150 °C	-	-	20	μA
		T _{mb} = 25 °C	-	0.1	1	μA
I _{L(off)}	off-state load current	V _{BL} = V _{BG} ; per channel				
		T _{mb} = 150 °C	-	-	10	μA
		T _{mb} = 25 °C	-	0.1	1	μA
I _{G(on)}	operating current	one channel on; Figure 5	-	2	3	mA
		both channels on	-	4	6	mA
I _{L(nom)}	nominal load current (ISO)	V _{BL} = 0.5 V; T _{mb} = 85 °C	[4] 3.6	-	-	A
Resistance						
R _{BLon}	battery-load on-state resistance	9 ≤ V _{BG} ≤ 35 V; I _L = 4 A; Figure 4	[5]			
		T _{mb} = 25 °C	-	73	90	mΩ
		T _{mb} = 150 °C	-	146	180	mΩ
		V _{BG} = 5.5 V; I _L = 4 A				
		T _{mb} = 25 °C	-	76	120	mΩ
		T _{mb} = 150 °C	-	150	240	mΩ
R _G	ground resistor	I _G = −200 mA; t _p = 300 μs	[6] 40	75	100	Ω
Input [7]						
I _I	input current	V _{IG} = 5 V	20	60	160	μA
V _{IG(CL)}	input-ground clamping voltage	I _I = 200 μA	5.5	7	8.5	V
V _{IG(on)}	input-ground turn-on voltage	Figure 8	-	2.1	3	V
V _{IG(off)}	input-ground turn-off voltage		1.2	1.8	-	V
V _{IG(on)(hys)}	input-ground turn-on hysteresis		0.15	0.3	0.5	V
I _{I(on)}	input turn-on current	V _{IG} = 3 V	-	-	100	μA
I _{I(off)}	input turn-off current	V _{IG} = 1.2 V	12	-	-	μA
Open current detection [8][9]						
V _{LG(oc)}	load-ground open circuit voltage	V _{BG} ≥ 9 V	1.5	2.5	3.5	V
I _{G(oc)}	open-circuit operating current	V _{BG} = V _{LG} = 16 V open load detected; other channel is off	-	0.8	1.5	mA

Table 6: Static characteristics...continuedLimits are valid for $-40\text{ }^{\circ}\text{C} \leq T_{mb} \leq +150\text{ }^{\circ}\text{C}$ and typical values for $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{L(oc)}$	load open circuit current	$V_{LG} = 3.5\text{ V}$; per channel	-	-22	-40	μA
		$V_{LG} = 16\text{ V}$; per channel	-	-200	-300	μA
$R_{L(oc)}$	open circuit load resistor	$V_S = 5\text{ V}$; connected externally; per channel; Figure 10	-	10	-	$\text{k}\Omega$
Undervoltage [9]						
$V_{BG(uv)}$	battery-ground undervoltage	[11]	2	4.2	5.3	V
$V_{BG(uv)(hys)}$	battery-ground undervoltage hysteresis		-	0.5	1.5	V
Overvoltage [9]						
$V_{BG(ov)}$	battery-ground overvoltage	[12]	35	40	45	V
$V_{BG(ov)(hys)}$	battery-ground overvoltage hysteresis		0.2	1	2	V
$I_{G(ov)}$	overvoltage operating current	$V_{BG} = 45\text{ V}$; per channel	-	1	2.5	mA
Overload protection						
$I_{L(lim)}$	self-limiting load current	$V_{BG} \geq 8\text{ V}$; $V_{BL} = V_{BG}$; Figure 7	8	12	16	A
Overtemperature protection [9][10]						
$T_{j(th)}$	threshold junction temperature	[13]	150	170	190	$^{\circ}\text{C}$
$T_{j(th)(hys)}$	threshold junction temperature hysteresis		3	10	20	$^{\circ}\text{C}$
Status [9]						
$V_{SG(CL)}$	status-ground clamping voltage	$I_S = 100\text{ }\mu\text{A}$	5.5	7	8.5	V
$V_{SG(L)}$	status-ground low voltage	$I_S = 100\text{ }\mu\text{A}$; Figure 6	-	0.7	0.9	V
		$I_S = 250\text{ }\mu\text{A}$	-	-	1.1	V
$I_{S(off)}$	status leakage current	$V_{SG} = 5\text{ V}$				
		$T_{mb} = 150\text{ }^{\circ}\text{C}$	-	-	10	μA
		$T_{mb} = 25\text{ }^{\circ}\text{C}$	-	0.1	1	μA
R_S	status resistor	$V_{SG} = 5\text{ V}$; connected externally; Figure 10 [14]	-	47	-	$\text{k}\Omega$

[1] For a high-side switch, the load pin voltage goes negative with respect to the ground during the turn-off of an inductive load. This negative voltage is clamped by the device.

[2] $9\text{ V} \leq V_{BG} \leq 35\text{ V}$

[3] This is the current drawn from the supply when both inputs are LOW, and includes leakage current to the loads.

[4] Defined as in ISO10483-1. For comparison purposes only.

[5] This only applies to the R_{BLon} per channel. The supply and input voltages for the R_{BLon} tests are continuous. The specified pulse duration is $t_p = 300\text{ }\mu\text{s}$, and refers only to the applied load current.

[6] R_G is a resistor incorporated internally into the package.

[7] $5.5\text{ V} \leq V_{BG} \leq 35\text{ V}$

[8] An open circuit load can be detected in the off-state and requires an external pull-up resistor, $R_{L(oc)}$.

[9] See **Table 3 "Truth table"**

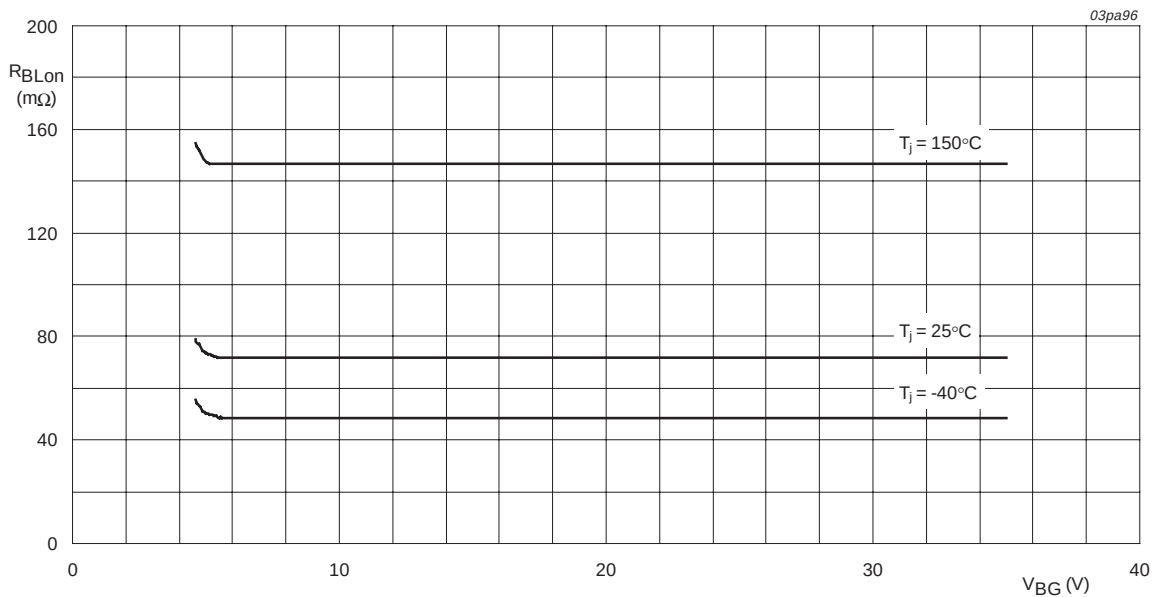
[10] Overtemperature protection is not active during reverse current operation.

[11] Undervoltage sensor causes each output channel to switch off and reset.

[12] Overvoltage sensor causes each output channel to switch off to protect the load.

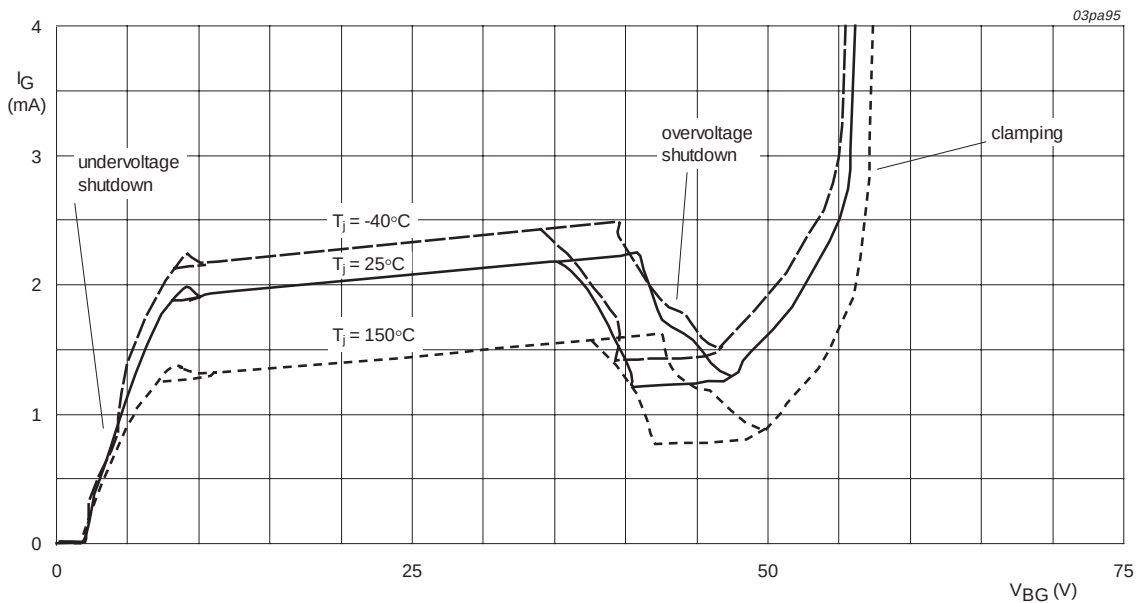
[13] After cooling below the reset temperature the channel will resume normal operation.

[14] The status output is an open drain transistor and requires an external pull-up resistor, R_S , to indicate a logic HIGH.



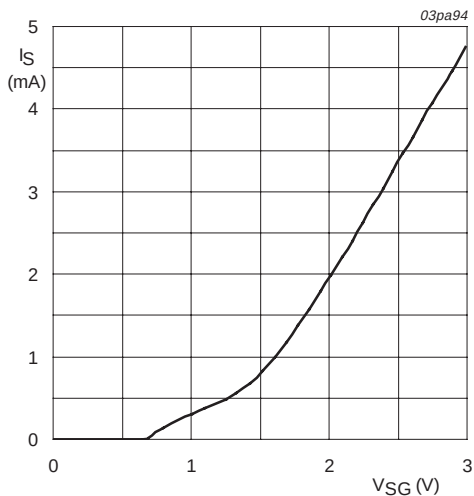
$I_L = 4$ A; $V_{IG} = 5$ V

Fig 4. Battery-load on-state resistance as a function of battery-ground voltage; typical values.



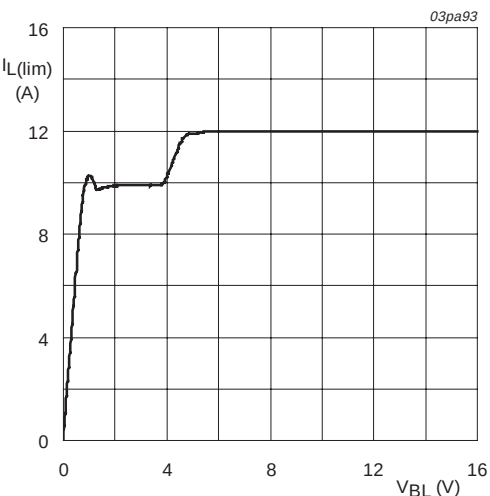
$V_{IG} = 5$ V

Fig 5. Supply current characteristics: operating current as a function of battery-ground voltage for one channel only; typical values.



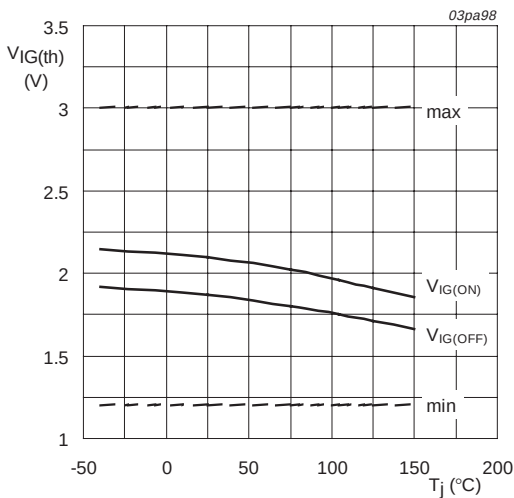
V_{BG} = 13 V; V_{IG} = 5 V; T_J = 25 °C

Fig 6. Status current as a function of status-ground voltage; typical values.



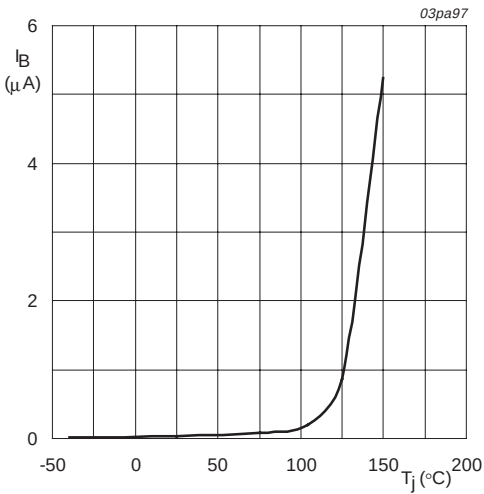
V_{BG} = 16 V; V_{IG} = 5 V; T_{mb} = 25 °C

Fig 7. Self-limiting load current as a function of battery-load voltage; typical values.



5.5 V ≤ V_{BG} ≤ 35 V

Fig 8. Input-ground threshold voltage as a function of junction temperature.



V_{BG} = 35 V

Fig 9. Battery quiescent current as a function of junction temperature; typical values.

8. Dynamic characteristics

Table 7: Switching characteristics

$T_{mb} = 25\text{ }^{\circ}\text{C}$; $V_{BG} = 13\text{ V}$; resistive load $R_L = 13\text{ }\Omega$ per channel; **Figure 12**.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Turn-on measured from the input going HIGH						
$t_{d(on)}$	turn-on delay time	to 10 % V_L	-	30	-	μs
dV/dt_{on}	rising slew rate	30 to 70 % V_L	0.5	1	2	$\text{V}/\mu\text{s}$
t_{on}	turn-on switching time	to 90 % V_L	-	60	220	μs
Turn-off measured from the input going LOW						
$t_{d(off)}$	turn-off delay time	to 90 % V_L	-	20	-	μs
dV/dt_{off}	falling slew rate	70 to 30 % V_L	0.5	1	2	$\text{V}/\mu\text{s}$
t_{off}	turn-off switching time	to 10 % V_L	-	40	200	μs

Table 8: Capacitances

$T_{mb} = 25\text{ }^{\circ}\text{C}$; $f = 1\text{ MHz}$; $V_{IG} = 0\text{ V}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{sg}	status-ground capacitance	$V_{SG} = 5\text{ V}$	-	11	15	pF
Per channel						
C_{ig}	input-ground capacitance	$V_{BG} = 13\text{ V}$	-	15	20	pF
C_{bl}	battery-load capacitance	$V_{BL} = 13\text{ V}$	-	130	180	pF

Table 9: Short circuit load protection characteristics

$T_{mb} \leq 125\text{ }^{\circ}\text{C}$ prior to the overload short circuit condition.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
P _{BL(OV)(th)}	battery-load overload power threshold	5.5 ≤ V _{BG} ≤ 35 V; device trips if P _{BL} > P _{BL(OV)(th)} ; Figure 11	[1]	10	55	100	W
t _{BL(d)(sc)}	battery-load short-circuit characteristic time		[2]	200	350	800	μs

[1] Short circuit protection is latched, but at high temperatures where $T_j > T_{j(th)}$ overtemperature protection may occur first. Normal operation may only be resumed following a short circuit after the input is toggled LOW then HIGH again.

[2] Short circuit response time $t_{d(sc)}$ varies with battery-load power P_{BL} according to the **logarithmic model** equation:

$$t_{d(sc)} \approx \frac{t_{BL(d)(sc)}}{\ln\left(\frac{P_{BL}}{P_{BL(OV)(th)}}\right)}$$

Table 10: Status response times

Limits are valid for $-40\text{ }^{\circ}\text{C} \leq T_{mb} \leq +150\text{ }^{\circ}\text{C}$ and typical values for $T_{mb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Measured from when the input goes LOW to when the status goes LOW						
$t_{d(oc)}$	open-circuit response time	Figure 10 and 14	-	65	100	μs

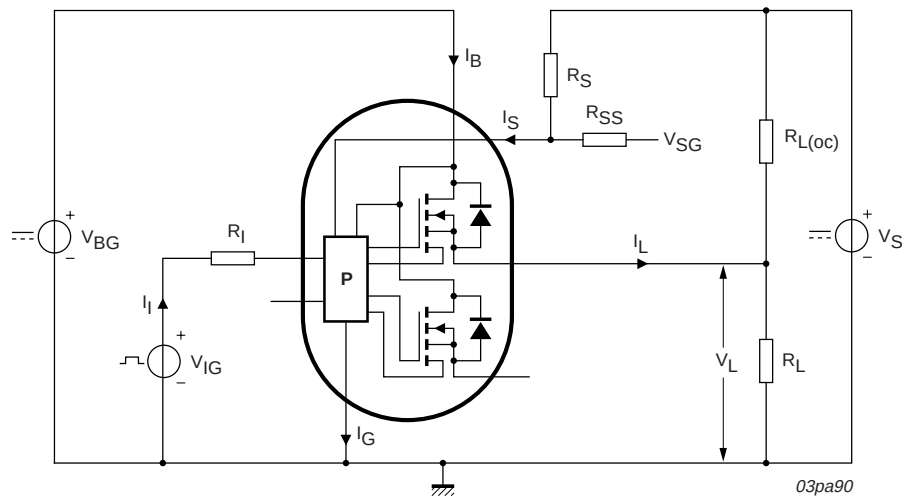

$$R_I \geq 3.3 \text{ k}\Omega; R_S = 47 \text{ k}\Omega; R_{SS} \geq 3.3 \text{ k}\Omega \text{ and } R_{L(oc)} = 10 \text{ k}\Omega.$$

Fig 10. Typical dynamic response circuit diagram including reverse supply protection and open load detection.

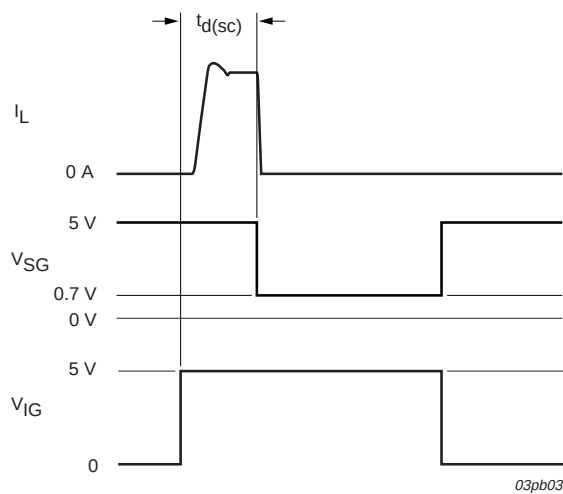


Fig 11. Short circuit protection waveforms.

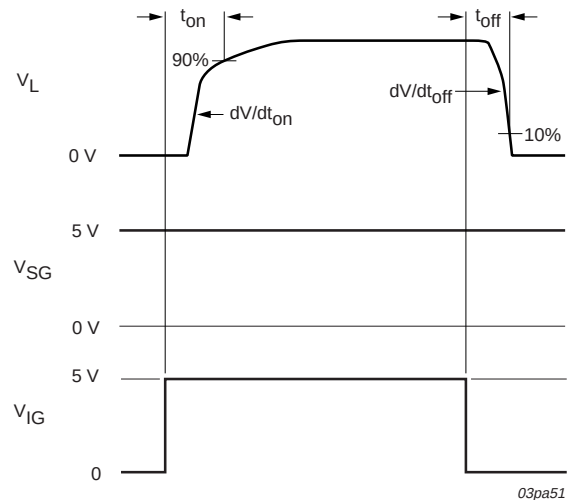

$$V_{BG} = 13 \text{ V}; V_{IG} = 5 \text{ V and } T_j = 25 \text{ }^\circ\text{C}$$

Fig 12. Resistive switching waveforms and definitions.

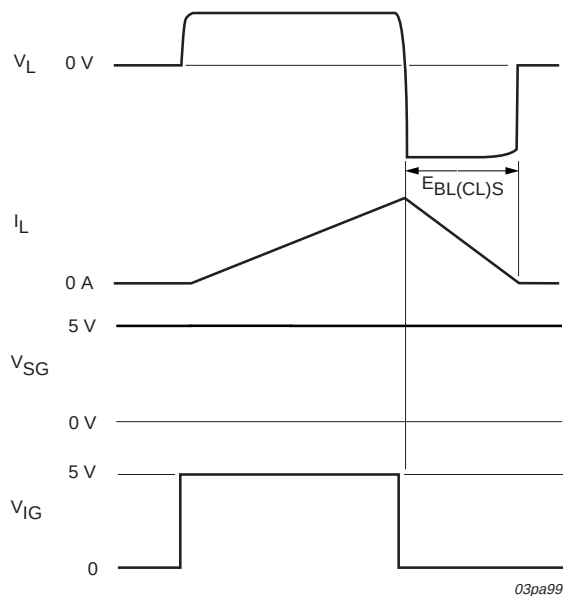


Fig 13. Switching a large inductive load.

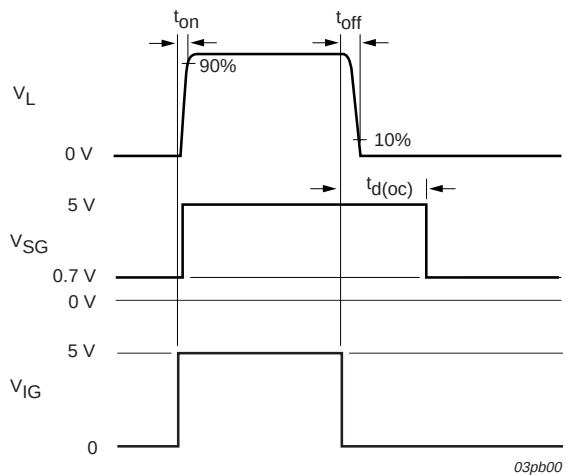
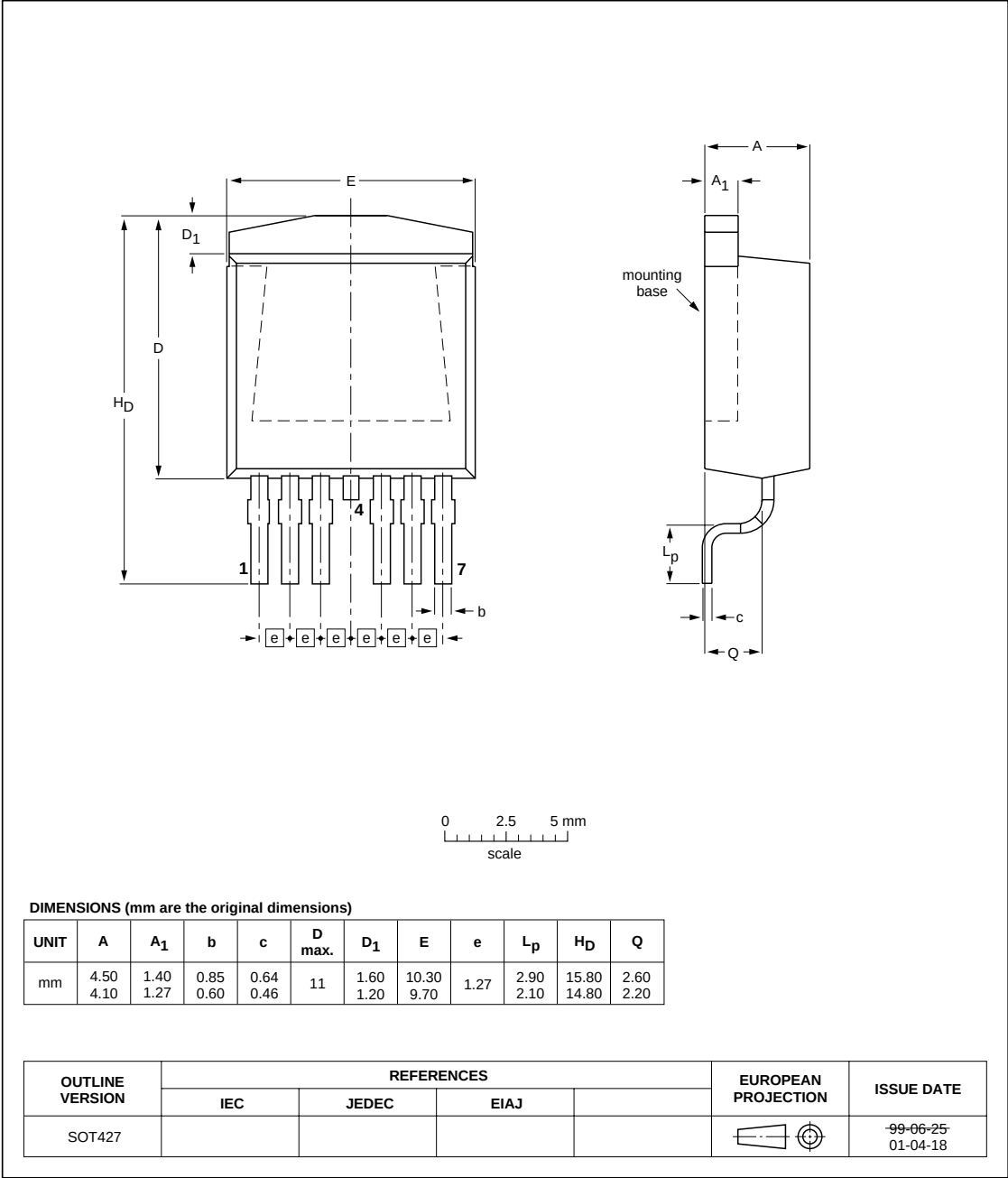


Fig 14. Open circuit detect waveforms.

9. Package outline

Plastic single-ended surface mounted package (Philips version of D²-PAK);
7 leads (one lead cropped) SOT427



Epoxy meets UL94 V0 at 1/8". Net mass: 1.5g. For soldering guidelines and surface mount footprint design, please refer to Data Handbook SC18.

Fig 15. SOT427 (D²-PAK).

10. Revision history

Table 11: Revision history

Rev	Date	CPCN	Description
01	20030416	-	Product data (9397 750 11167)

11. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2][3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

12. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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